

## Features

- N-Channel, 5V Logic Level Control
- Enhancement mode
- Very low on-resistance
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant



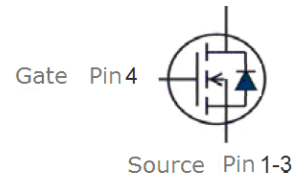
| Part ID     | Package Type | Marking | Tape and reel information |
|-------------|--------------|---------|---------------------------|
| VSP005N06MS | PDFN5x6      | 005N06M | 3000pcs/Reel              |

|                               |     |            |
|-------------------------------|-----|------------|
| $V_{DS}$                      | 60  | V          |
| $R_{DS(on),TYP@ V_{GS}=10V}$  | 3.8 | m $\Omega$ |
| $R_{DS(on),TYP@ V_{GS}=4.5V}$ | 4.9 | m $\Omega$ |
| $I_D$                         | 125 | A          |

### PDFN5x6



Drain Pin5-8



## Maximum ratings, at $T_j=25^\circ\text{C}$ , unless otherwise specified

| Symbol        | Parameter                               | Rating                        | Unit             |
|---------------|---|-------------------------------|------------------|
| $V_{(BR)DSS}$ | Drain-Source breakdown voltage          | 60                            | V                |
| $I_S$         | Diode continuous forward current        | $T_C=25^\circ\text{C}$<br>125 | A                |
| $I_D$         | Continuous drain current@ $V_{GS}=10V$  | $T_C=25^\circ\text{C}$<br>125 | A                |
|               |   | $T_C=100^\circ\text{C}$<br>79 | A                |
| $I_{DM}$      | Pulse drain current tested ①            | $T_C=25^\circ\text{C}$<br>400 | A                |
| EAS           | Avalanche energy, single pulsed ②       | 100                           | mJ               |
| $P_D$         | Maximum power dissipation               | $T_C=25^\circ\text{C}$<br>125 | W                |
| $V_{GS}$      | Gate-Source voltage                     | $\pm 20$                      | V                |
| $T_{STG} T_J$ | Storage and operating temperature range | -55 to 150                    | $^\circ\text{C}$ |

## Thermal Characteristics

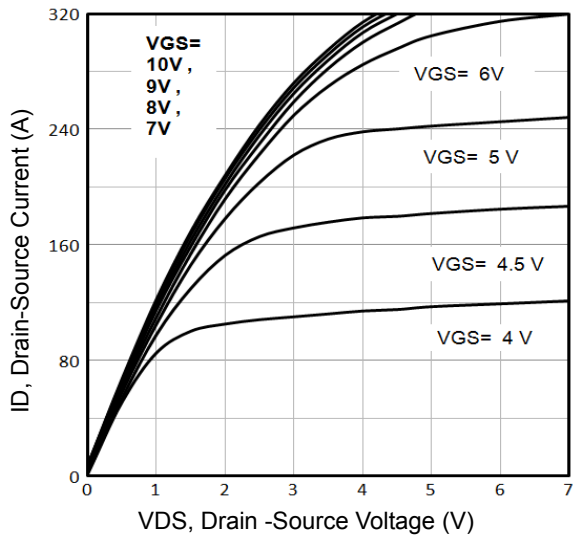
| Symbol          | Parameter                           | Typical | Unit               |
|-----------------|-------------------------------------|---------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case | 1.0     | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient | 45      | $^\circ\text{C/W}$ |

| Symbol  | Parameter  | Condition  | Min. | Typ. | Max. | Unit |
|---|--|--|------|------|------|------|
| <b>Static Electrical Characteristics @ T<sub>c</sub> = 25°C (unless otherwise stated)</b>   |  |  |      |      |      |      |
| V <sub>(BR)DSS</sub>  | Drain-Source Breakdown Voltage                         | V <sub>GS</sub> =0V I <sub>D</sub> =250μA  | 60   | --   | --   | V    |
| I <sub>DSS</sub>  | Zero Gate Voltage Drain Current(T <sub>c</sub> =25°C)  | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V  | --   | --   | 1    | μA   |
|   | Zero Gate Voltage Drain Current(T <sub>c</sub> =125°C) | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V  | --   | --   | 100  | μA   |
| I <sub>GSS</sub>  | Gate-Body Leakage Current                              | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   | --   | --   | ±100 | nA   |
| V <sub>GS(TH)</sub>   | Gate Threshold Voltage                                 | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                       | 1.0  | 2.0  | 3.0  | V    |
| R <sub>DS(ON)</sub>   | Drain-Source On-State Resistance <sup>③</sup>          | V <sub>GS</sub> =10V, I <sub>D</sub> =30A  | --   | 3.8  | 5.0  | mΩ   |
| R <sub>DS(ON)</sub>   | Drain-Source On-State Resistance <sup>③</sup>          | V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A   | --   | 4.9  | 6.0  | mΩ   |
| <b>Dynamic Electrical Characteristics @ T<sub>c</sub> = 25°C (unless otherwise stated)</b>  |  |  |      |      |      |      |
| C <sub>iss</sub>  | Input Capacitance                                      | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,<br>f=1MHz   | --   | 4980 | --   | pF   |
| C <sub>oss</sub>  | Output Capacitance                                     |  | --   | 505  | --   | pF   |
| C <sub>rss</sub>  | Reverse Transfer Capacitance                           |  | --   | 450  | --   | pF   |
| R <sub>g</sub>  | Gate Resistance  | f=1MHz   | --   | 1.55 | --   | Ω    |
| Q <sub>g</sub>  | Total Gate Charge                                      | V <sub>DS</sub> =30V, I <sub>D</sub> =20A,<br>V <sub>GS</sub> =10V                             | --   | 120  | --   | nC   |
| Q <sub>gs</sub>   | Gate-Source Charge                                     |  | --   | 17   | --   | nC   |
| Q <sub>gd</sub>   | Gate-Drain Charge                                      |  | --   | 37   | --   | nC   |
| <b>Switching Characteristics</b>  |  |  |      |      |      |      |
| t <sub>d(on)</sub>  | Turn-on Delay Time                                     | V <sub>DD</sub> =30V,<br>I <sub>D</sub> =10A,<br>R <sub>G</sub> =3.5Ω,<br>V <sub>GS</sub> =10V | --   | 19   | --   | nS   |
| t <sub>r</sub>  | Turn-on Rise Time                                      |  | --   | 14   | --   | nS   |
| t <sub>d(off)</sub>   | Turn-Off Delay Time                                    |  | --   | 65   | --   | nS   |
| t <sub>f</sub>  | Turn-Off Fall Time                                     |  | --   | 16   | --   | nS   |
| <b>Source- Drain Diode Characteristics @ T<sub>c</sub> = 25°C (unless otherwise stated)</b> |  |  |      |      |      |      |
| V <sub>SD</sub>   | Forward on voltage                                     | I <sub>SD</sub> =30A, V <sub>GS</sub> =0V  | --   | 0.79 | 1.0  | V    |
| t <sub>rr</sub>   | Reverse Recovery Time                                  | T <sub>j</sub> =25°C, I <sub>sd</sub> =20A,<br>di/dt=500A/μs                                   | --   | 42   | --   | nS   |
| Q <sub>rr</sub>   | Reverse Recovery Charge                                |  | --   | 145  | --   | nC   |

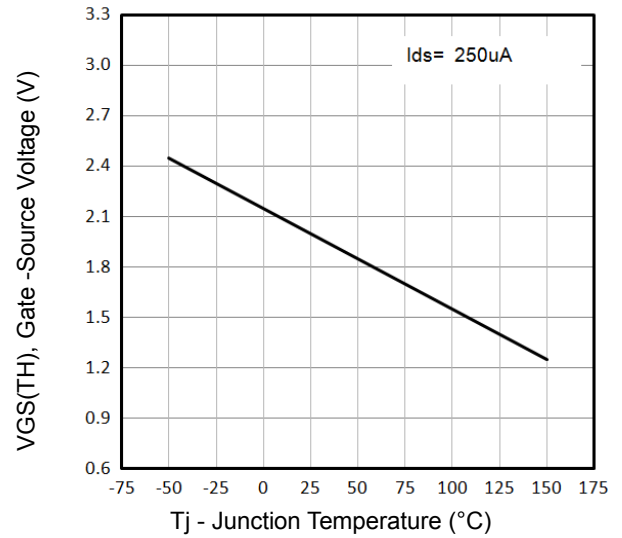
**NOTE:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 0.5mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 20A, V<sub>GS</sub> = 10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

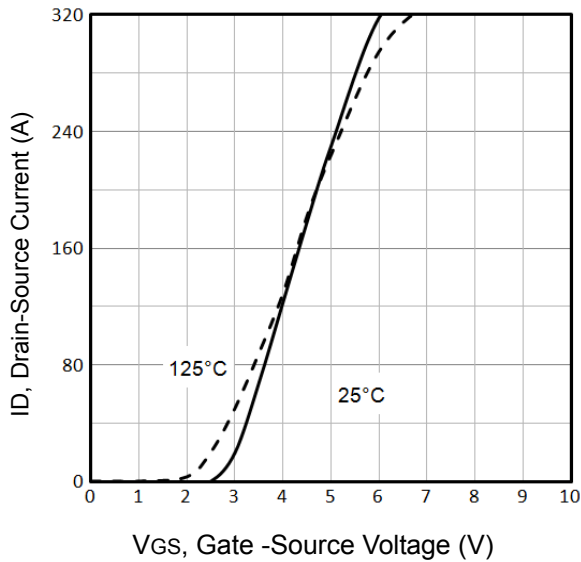
**Typical Characteristics**



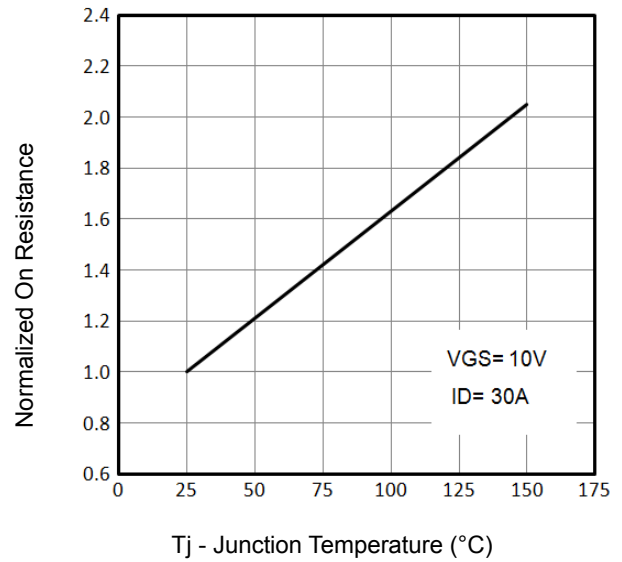
**Fig1.** Typical Output Characteristics



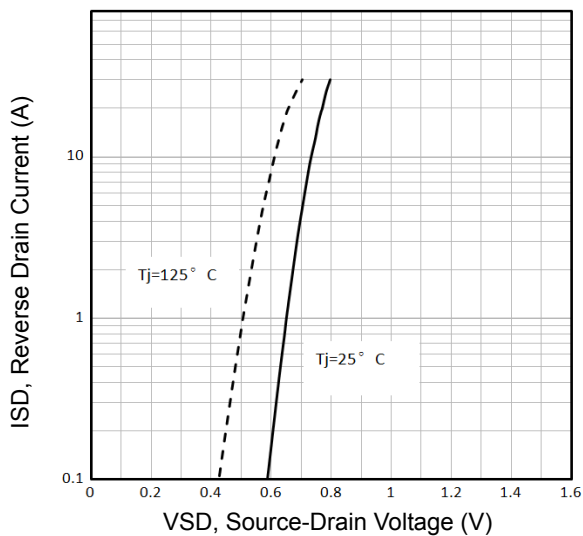
**Fig2.**  $V_{GS(TH)}$  Gate-Source Voltage Vs.  $T_j$



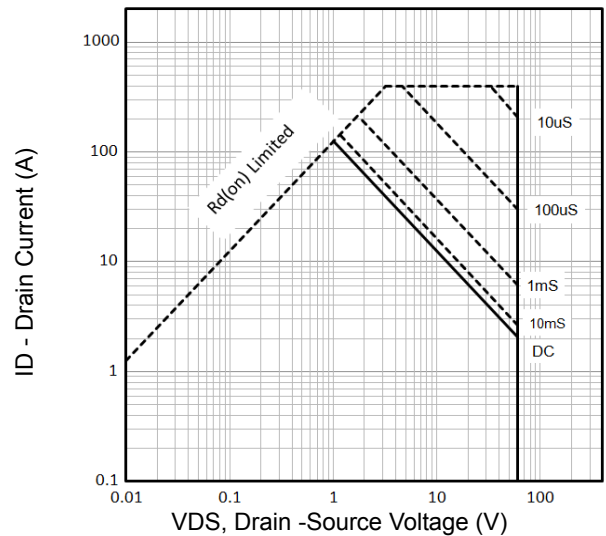
**Fig3.** Typical Transfer Characteristics



**Fig4.** Normalized On-Resistance Vs.  $T_j$



**Fig5.** Typical Source-Drain Diode Forward Voltage



**Fig6.** Maximum Safe Operating Area

Typical Characteristics

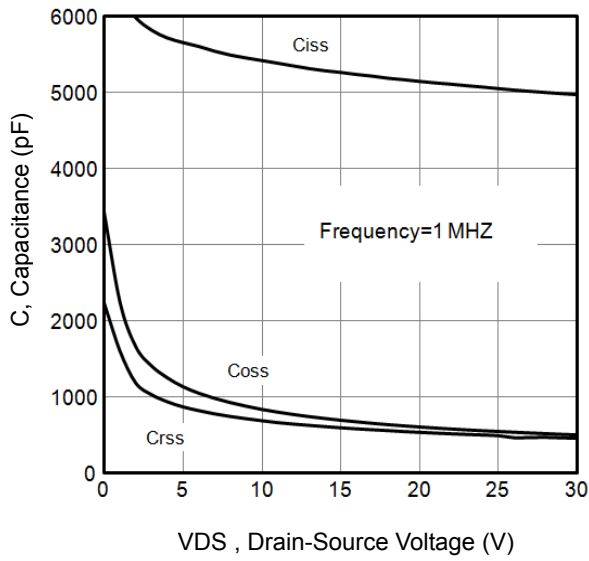


Fig7. Typical Capacitance Vs. Drain-Source Voltage

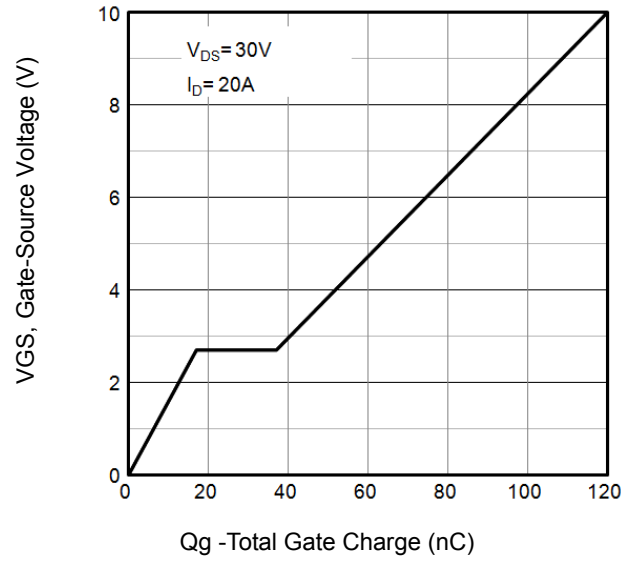


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

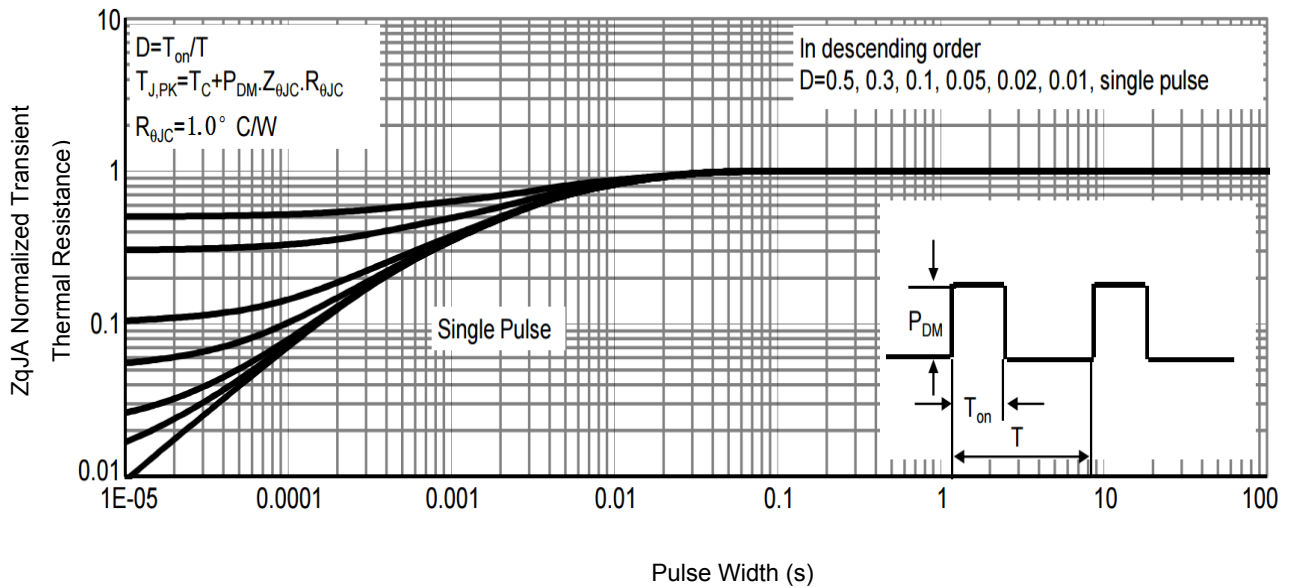


Fig9 . Normalized Maximum Transient Thermal Impedance

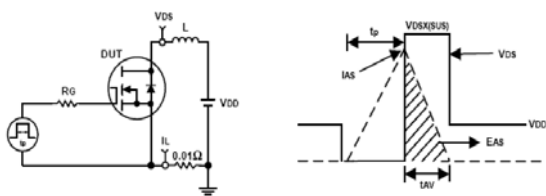


Fig10. Unclamped Inductive Test Circuit and waveforms

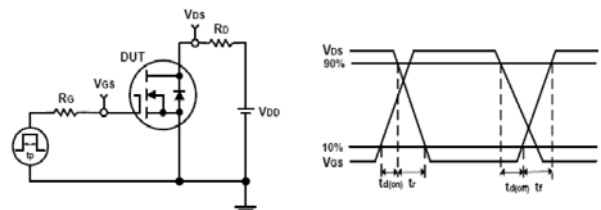
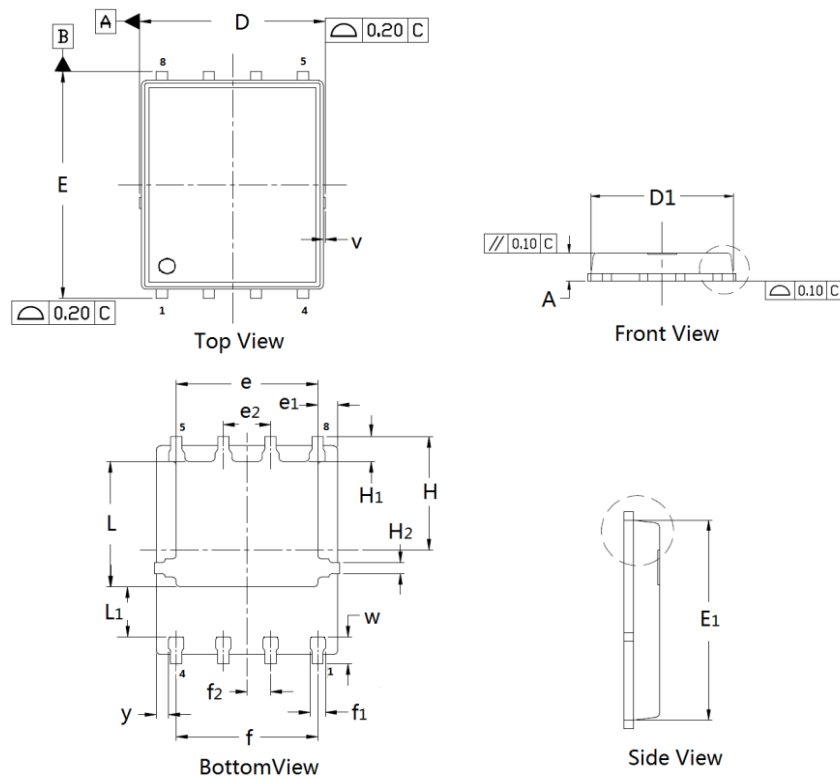


Fig11. Switching Time Test Circuit and waveforms

**PDFN5×6 Package Outline Data**

**DIMENSIONS ( unit : mm )**

| Symbol         | Min  | Typ  | Max  | Symbol         | Min  | Typ  | Max  |
|----------------|------|------|------|----------------|------|------|------|
| A              | 0.90 | 1.02 | 1.10 | D              | 4.90 | 4.98 | 5.10 |
| D <sub>1</sub> | 4.80 | 4.89 | 5.00 | E              | 6.00 | 6.11 | 6.20 |
| E <sub>1</sub> | 5.65 | 5.74 | 5.85 | e              | 3.72 | 3.80 | 3.92 |
| e <sub>1</sub> | --   | 0.54 | --   | e <sub>2</sub> | --   | 1.27 | --   |
| f              | --   | 3.82 | --   | f <sub>1</sub> | 0.31 | 0.37 | 0.51 |
| f <sub>2</sub> | --   | 0.64 | --   | H              | --   | 3.15 | --   |
| H <sub>1</sub> | 0.59 | 0.63 | 0.79 | H <sub>2</sub> | 0.26 | 0.28 | 0.32 |
| L              | 3.38 | 3.45 | 3.58 | L <sub>1</sub> | --   | 1.39 | --   |
| v              | --   | 0.13 | --   | w              | 0.64 | 0.68 | 0.84 |
| y              | --   | 0.34 | --   |                | --   |      | --   |

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